TOSHIBA 155200

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155200

ULTRA HIGH SPEED SWITCHING APPLICATION.

Low Forward Voltage $: V_{F(3)} = 0.92V \text{ (Typ.)}$

• Fast Reverse Recovery Time: trr=1.6ns (Typ.)

• Small Total Capacitance : C_T=2.2pF (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	v_{RM}	85	V
Reverse Voltage	$V_{\mathbf{R}}$	80	V
Maximum (Peak) Forward Current	I_{FM}	300 (*)	mA
Average Forward Current	IO	100 (*)	mA
Surge Current (10ms)	I_{FSM}	2 (*)	Α
Power Dissipation	P	200	mW
Junction Temperature	T_{j}	125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Unit in mm

4.2MAX

0.55MAX

1.271.27

25°

1. CATHODE 1
2. ANODE 1, 2
3. CATHODE 2

JEDEC

EIAJ

—

Unit in mm

1-4E2B

TOSHIBA

Weight: 0.13g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

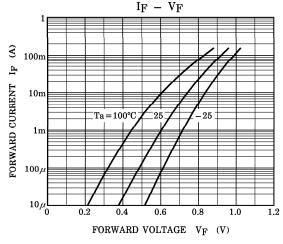
(*) Unit Rating. Total Rating=Unit Rating×1.5.

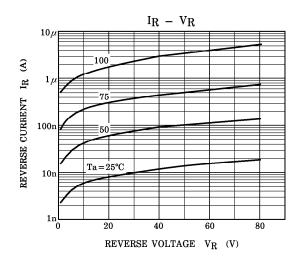
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{F (1)}	I _F =1mA		0.61	_	V
	$V_{F(2)}$	$I_{ m F}$ = 10mA	_	0.74	_	
	$V_{F(3)}$	$I_{ m F}\!=\!100{ m mA}$	_	0.92	1.20	
Reverse Current $\frac{I_{R(1)}}{I_{R(2)}}$	I _{R (1)}	$V_R = 30V$	_	_	0.1	μ A
	$I_{R(2)}$	$V_R = 80V$	_	_	0.5	
Total Capacitance	C_{T}	$V_R=0$, f=1MHz		2.2	4.0	pF
Reverse Recovery Time	t_{rr}	I _F =10mA (Fig.1)	_	1.6	4.0	ns

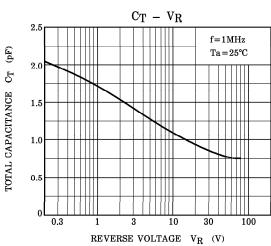
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TOSHIBA 1SS200







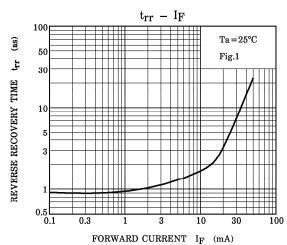
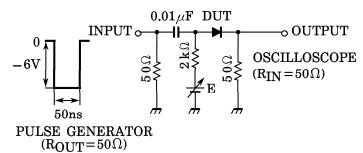
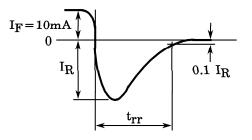


Fig.1 Reverse recovery time (t_{rr}) test circuit

INPUT WAVEFORM

OUTPUT WAVEFORM





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